

2N7002E

Silicon N-channel MOSFET

For switching circuits

Panasonic parts No. FK360602

■ Features

- Low Drain-source On-state Resistance : $R_{DS(on)}$ typ = $1\ \Omega$ ($V_{GS} = 4.5\ V$)
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : GV

■ Packaging

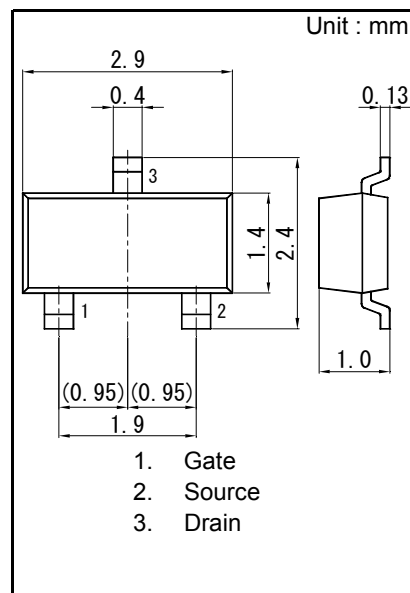
Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\ ^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	V_{DS}	60	V
Gate to Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	300	mA
Drain Current (Pulsed) ^{*1}	I_{Dp}	600	mA
Total Power Dissipation ^{*2}	PD	350	mW
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

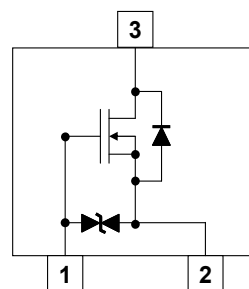
Note *1 Pulse test: Ensure that the channel temperature does not exceed $150\ ^\circ\text{C}$

*2 Mounted on FR4 board ($25.4\text{mm} \times 25.4\text{mm} \times 0.8\text{mm}$, Cu area $> 300\text{mm}^2$)



Panasonic	NMini3-R1-B
JEITA	SC-59A
Code	TO-236AA/SOT-23

Internal Connection



Pin Name

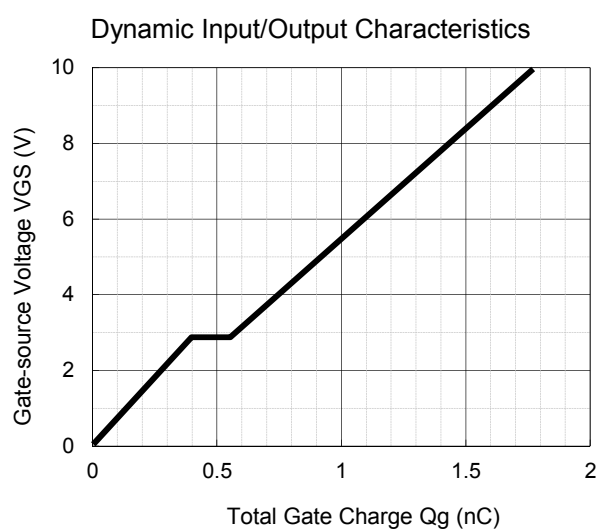
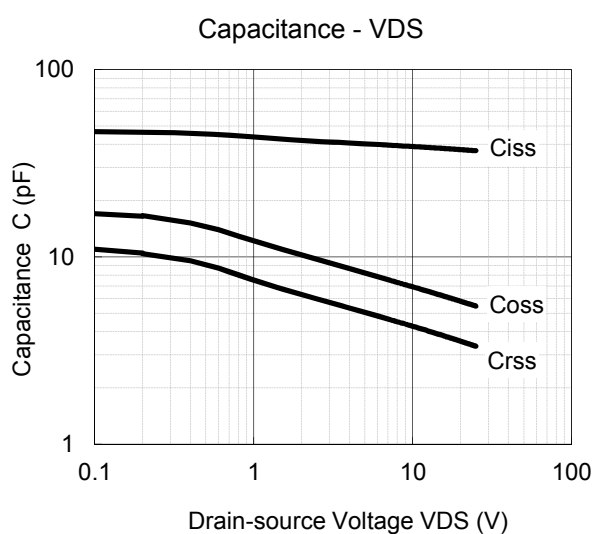
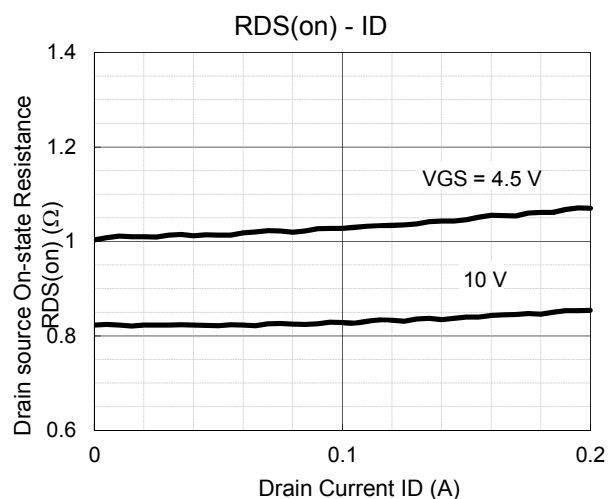
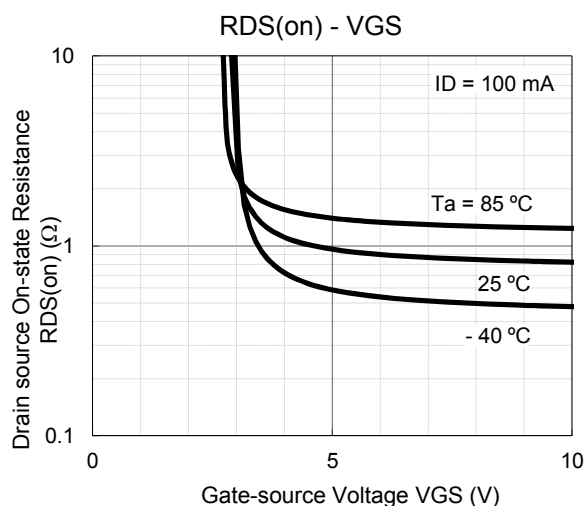
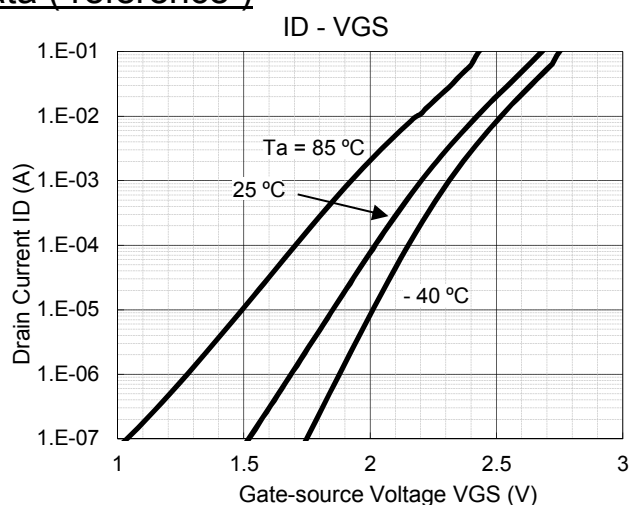
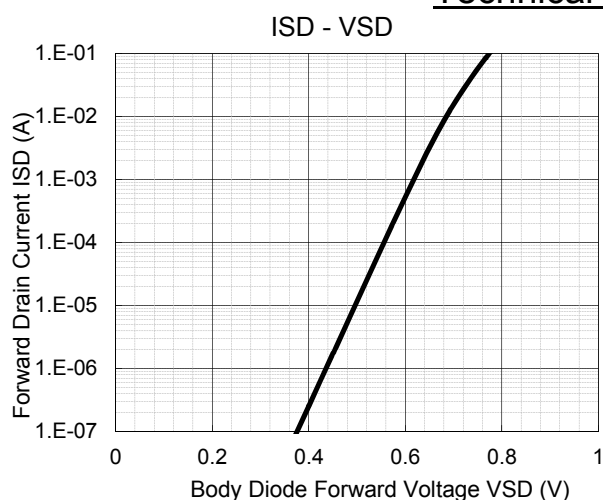
1. Gate
2. Source
3. Drain

■ Electrical Characteristics Ta = 25 °C ± 3 °C

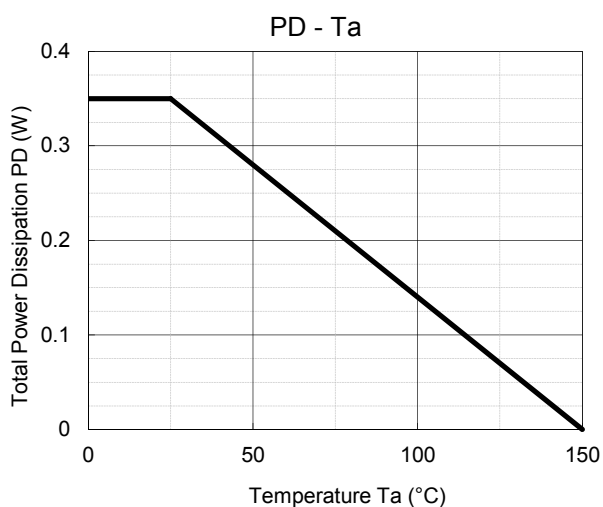
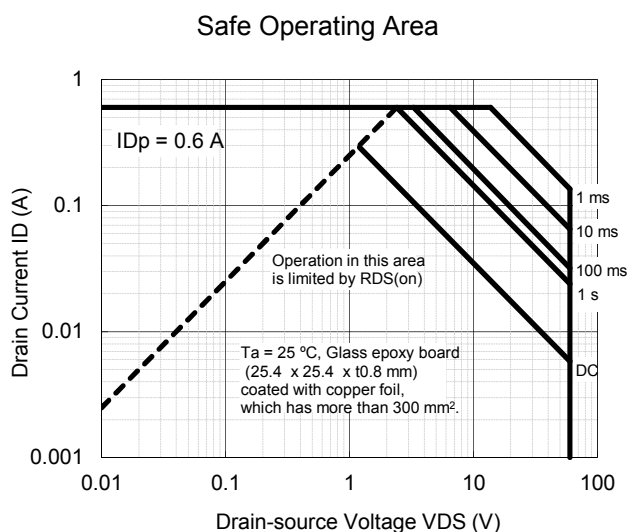
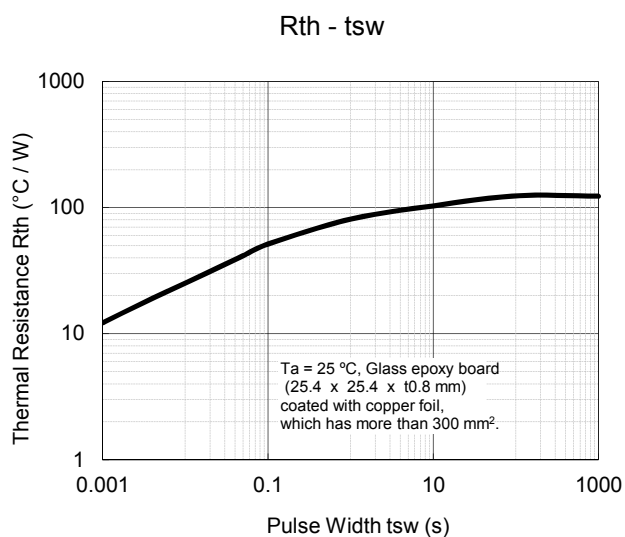
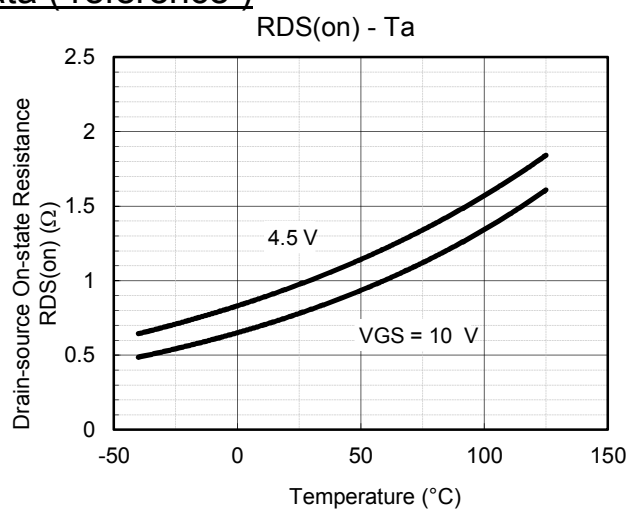
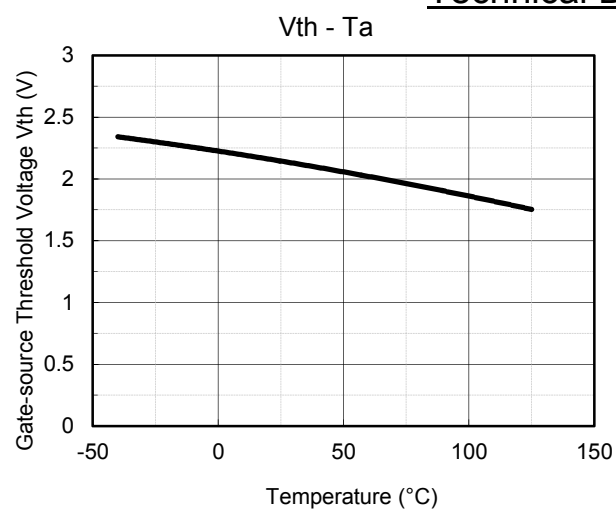
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 250 μ A, VGS = 0 V	60			V
Zero Gate Voltage Drain Current	IDSS	VDS = 60 V, VGS = 0 V			1	μ A
Gate-source Leakage Current	IGSS	VGS = \pm 20 V, VDS = 0 V			\pm 10	μ A
Gate-source Threshold Voltage	Vth	ID = 250 μ A, VDS = 10 V	1		3	V
Drain-source On-state Resistance	RDS(on)1	ID = 100 mA, VGS = 10 V		0.8	3	Ω
	RDS(on)2	ID = 100 mA, VGS = 4.5 V		1	4	
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V f = 1 MHz		40		pF
Output Capacitance	Coss			7		
Reverse Transfer Capacitance	Crss			4.5		
Total Gate Charge	Qg	VDS = 10 V, VGS = 0 to 4.5 V ID = 200 mA		0.8		nC
Gate to Source Charge	Qgs			0.2		
Gate to Drain Charge	Qgd			0.4		

Note : Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

Technical Data (reference)



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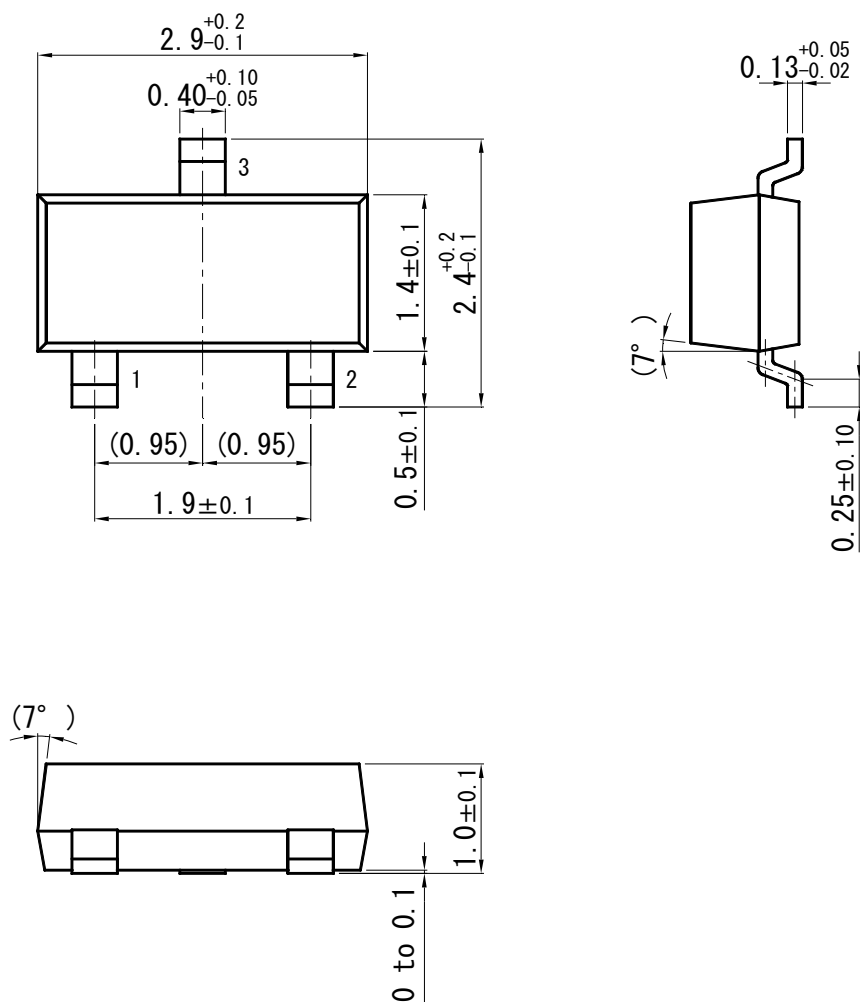


Panasonic

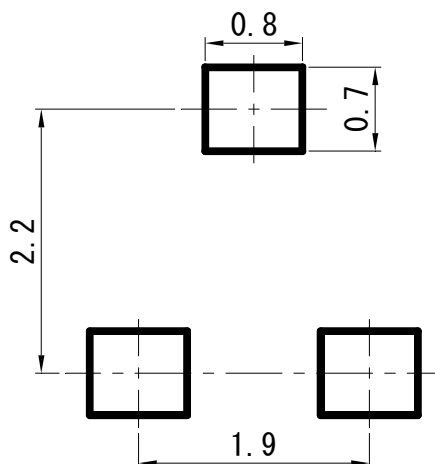
MOS FET
2N7002E

NMini3-R1-B

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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